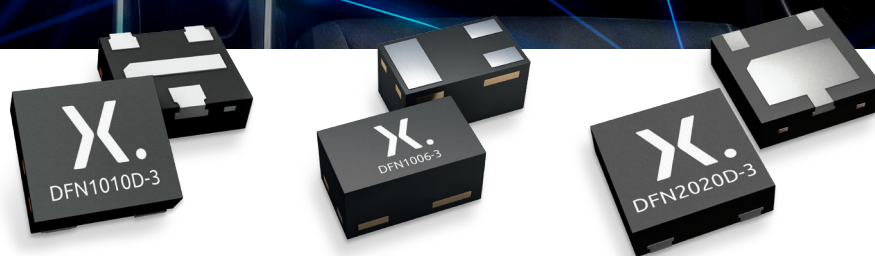


Power Transistors

Save space and minimize weight while ensuring the performance and efficiency



Low V_{CEsat} power transistors in DFN packages

Product	DFN2020D-3	DFN2020-3	DFN2020D-6	DFN2020-6	DFN1010D-3	DFN1006-3	DFN1006B-3
Size (mm)	2 x 2 x 0.65	2 x 2 x 0.65	2 x 2 x 0.65	2 x 2 x 0.65	1.1 x 1 x 0.37	1 x 0.6 x 0.48	1 x 0.6 x 0.37

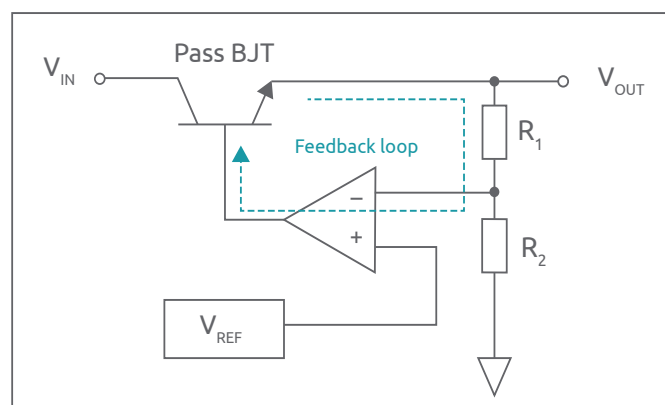
Key features and benefits

- › Low collector-emitter saturation voltage V_{CEsat}
- › High collector current capability I_C and I_{CM}
- › High collector current gain (h_{FE}) at high I_C
- › High efficiency due to less heat generation
- › Less power consumption due to low internal resistance R_{CEsat}
- › 175°C Parts available
- › Reduced Printed-Circuit Board (PCB) area requirements
- › Leadless small SMD plastic package
- › Parts with solderable side pads available - Suitable for Automatic Optical Inspection (AOI) of solder joint
- › Automotive and non-Automotive parts

Key applications

- › Linear voltage regulation
- › Loadswitch
- › Battery-driven devices
- › Power management
- › Charging circuits
- › Power switches

Application example: Low V_{CEsat} Transistor PBSS4310PAS-Q as a Pass BJT in an LDO



Learn more

Scan the QR-code to learn more about Nexperia's portfolio of bipolar transistors

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EFFICIENCY WINS.